

MOS TRANSISTOR WITH HIGHLY LOCALIZED SUPER HALO IMPLANT

ABSTRACT OF THE DISCLOSURE

A method for improving the channel doping profile of deep-submicron field effect transistors and MOSFETs. The method involves a highly localized halo implant formed in the channel region but not in the source/drain junction. The halo implant is performed through a gap formed by removal of a temporary spacer. The MOSFET is then further completed.

SCANNED, # 1